Low Capacitance Diode Array for ESD Protection in Four Data Lines

NUP4301MR6T1 is a MicroIntegration[™] device designed to provide protection for sensitive components from possible harmful electrical transients; for example, ESD (electrostatic discharge).

Features

- Low Capacitance (1.5 pf Maximum Between I/O Lines)
- Single Package Integration Design
- Provides ESD Protection for JEDEC Standards JESD22 Machine Model = Class C Human Body Model = Class 3B
- Protection for IEC61000-4-2 (Level 4) 8.0 kV (Contact) 15 kV (Air)
- Ensures Data Line Speed and Integrity
- Fewer Components and Less Board Space
- Direct the Transient to Either Positive Side or to the Ground

Applications

- USB 1.1 and 2.0 Data Line Protection
- T1/E1 Secondary IC Protection
- T3/E3 Secondary IC Protection
- HDSL, IDSL Secondary IC Protection
- Video Line Protection
- Microcontroller Input Protection
- Base Stations
- I²C Bus Protection

MAXIMUM RATINGS (Each Diode) ($T_J = 25^{\circ}C$ unless otherwise noted)

Rating	Symbol	Value	Unit		
Reverse Voltage	V _R	70	Vdc		
Forward Current	١ _F	200	mAdc		
Peak Forward Surge Current	I _{FM(surge)}	500	mAdc		
Repetitive Peak Reverse Voltage	V _{RRM}	70	V		
Average Rectified Forward Current (Note 1) (averaged over any 20 ms period)	I _{F(AV)}	715	mA		
Repetitive Peak Forward Current	I _{FRM}	450	mA		
Non-Repetitive Peak Forward Current $t = 1.0 \ \mu s$ $t = 1.0 \ ms$ $t = 1.0 \ S$	I _{FSM}	2.0 1.0 0.5	A		

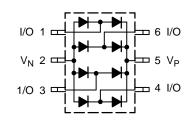
1. FR-5 = 1.0 \times 0.75 \times 0.062 in.

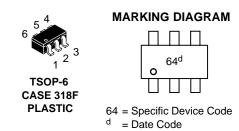


ON Semiconductor[®]

http://onsemi.com

PIN CONFIGURATION AND SCHEMATIC





ORDERING INFORMATION

Device	Package	Shipping
NUP4301MR6T1	TSOP-6	3000/Tape & Reel

THERMAL CHARACTERISTICS

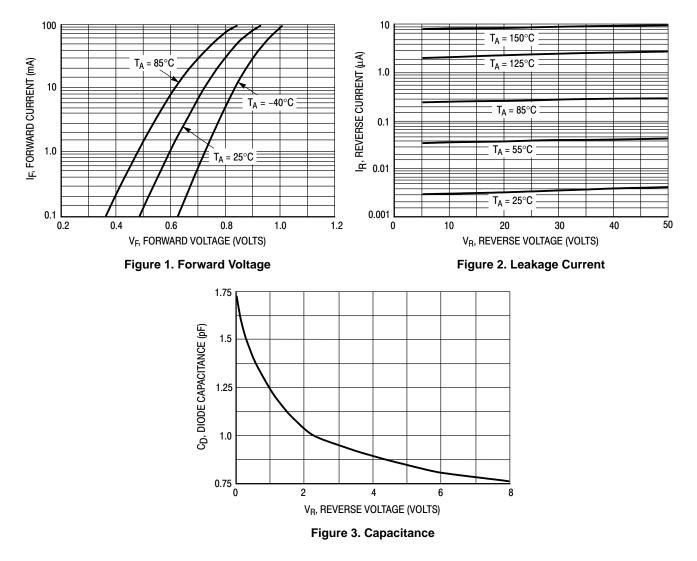
Characteristic	Symbol	Max	Unit
Thermal Resistance Junction-to-Ambient	$R_{ heta JA}$	556	°C/W
Lead Solder Temperature Maximum 10 Seconds Duration	TL	260	٥C
Junction Temperature	TJ	-40 to +85	°C
Storage Temperature	T _{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise noted) (Each Diode)

Characteristic	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						
Reverse Breakdown Voltage ($I_{(BR)} = 100 \ \mu A$)	V _(BR)	70	-	-	Vdc	
Reverse Voltage Leakage Current $(V_R = 70 \text{ Vdc})$ $(V_R = 25 \text{ Vdc}, T_J = 150^{\circ}\text{C})$ $(V_R = 70 \text{ Vdc}, T_J = 150^{\circ}\text{C})$	۱ _R	- -	- -	2.5 30 50	μAdc	
Capacitance (between I/O pins) ($V_R = 0 V$, f = 1.0 MHz)	CD	-	0.8	1.5	pF	
Capacitance (between I/O pin and ground) $(V_R = 0 V, f = 1.0 MHz)$	CD	-	1.6	3	pF	
Forward Voltage $ \begin{array}{c} (I_F = 1.0 \text{ mAdc}) \\ (I_F = 10 \text{ mAdc}) \\ (I_F = 50 \text{ mAdc}) \\ (I_F = 150 \text{ mAdc}) \end{array} $	V _F	- - - -	- - - -	715 855 1000 1250	mV _{dc}	

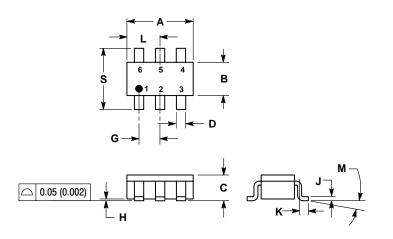
1. FR-5 = $1.0 \times 0.75 \times 0.062$ in. 2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.

Curves Applicable to Each Cathode



PACKAGE DIMENSIONS





NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH. MAXIMUM LEAD THICKNESS INCLUDES 2 3. LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 318F-01, -02, -03 OBSOLETE. NEW STANDARD 318F-04. 4.

	INC	HES	MILLIN	ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.1142	0.1220	2.90	3.10
В	0.0512	0.0669	1.30	1.70
С	0.0354	0.0433	0.90	1.10
D	0.0098	0.0197	0.25	0.50
G	0.0335	0.0413	0.85	1.05
н	0.0005	0.0040	0.013	0.100
J	0.0040	0.0102	0.10	0.26
К	0.0079	0.0236	0.20	0.60
L	0.0493	0.0649	1.25	1.65
М	0 °	10 °	0 °	10 °
S	0.0985	0.1181	2.50	3.00

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